

- ↳ L23: (164) 19 near 22
- ↳ L24: (918848) gate
- ↳ L25: (10104) (charge near3 (strap\$4 trap\$4 nitride))
- ↳ L27: (0) 23 with 25
- ↳ L28: (329) 19 with 22
- ↳ L29: (0) 28 with 25
- ↳ L30: (0) 28 same 25
- ↳ L26: (31) 23 with 24
- ↳ L31: (27) 28 and 25
- ↳ Failed
 - ↳ (silicon adj dioxide) SiO "SiO.sub.2"
- ↳ Saved
 - ↳ S2: (1) 09/948877
 - ↳ S3: (1736) "KONINKLIJKE PHILIPS".as.
 - ↳ S1: (0) 10/753914
 - ↳ S4: (2) "6750066" PN.
 - ↳ S5: (0) 10/775908
 - ↳ S6: (730) NROM
 - ↳ S7: (282581) (silicon adj dioxide SiO "SiO.sub.2")
 - ↳ S8: (100361) (dielectric adj constant relative adj (permittivit\$3 permittivit\$3)
 - ↳ S9: (98333) (dielectric adj constant relative adj (permittivit\$3 permittivit\$3)
 - ↳ S10: (4349) high adj k
 - ↳ S11: (25178) high near S9
 - ↳ S12: (28017) S10 S11

23 with 24

Feb. 2005

U	Inventor	Document Issue P	Title	Current X	Retrieval S	C	P	Image	Do	P
1	<input type="checkbox"/> Lei, Tan Fu	US 200401:2004 9	Process of utilizing CF4 plasma pretreatment	438/28	438/591	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
2	<input type="checkbox"/> Paranjpe, AUS	2003030:2003 1	Atomic layer deposition for fabricating	438/14	257/E21.2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030
3	<input type="checkbox"/> Min, Yo Se	US 666999:2003 1	Atomic layer deposition method using	427/25	427/255.3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 66699
4	<input type="checkbox"/> Rausch, W	US 200402:2004 1	Method of forming precision recessed	438/19	438/482	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
5	<input type="checkbox"/> Aoyama, S	US 200402:2004 5	Method and device for processing sub	438/88		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
6	<input type="checkbox"/> Conley, Jo	US 200402:2004 1	Modulated temperature method of ato	438/77	439/782	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
7	<input type="checkbox"/> Yeo, Yee-C	US 200401:2004 1	Semiconductor chip with gate dielectri	257/50		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
8	<input type="checkbox"/> Bude, Jeff	US 200401:2004 3	Semiconductor devices with reduced	438/93	257/431	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
9	<input type="checkbox"/> Jang, Chuc	US 200400:2004 1	Atomic layer deposition of interpoly oxi	257/31	257/E21.2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
10	<input type="checkbox"/> Lee, Yun-J	US 200400:2004 2	Method of forming oxide layer using at	438/75	257/E21.2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040